

N-channel 60 V, 3.4 mΩ logic level MOSFET in SOT78 7 February 2013 Product data sheet

1. General description

Logic level N-channel MOSFET in SOT78 using TrenchMOS technology. Product design and manufacture has been optimized for use in battery operated power tools.

2. Features and benefits

- High efficiency due to low switching & conduction losses
- Robust construction for demanding applications
- Logic level gate

3. Applications

- Battery-powered tools
- Load switching
- Motor control
- Uninterruptible power supplies

4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	60	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	[1]	-	-	130	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	293	W
Static chara	cteristics	•					,
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11		-	2.7	3.4	mΩ
Dynamic cha	aracteristics						
Q _{G(tot)}	total gate charge	V_{GS} = 10 V; I _D = 25 A; V _{DS} = 48 V;		-	175	-	nC
Q _{GD}	gate-drain charge	<u>Fig. 13; Fig. 14</u>		-	31	-	nC
Avalanche r	uggedness		1				
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$ I_D = 130 \text{ A}; V_{sup} \le 60 \text{ V}; \text{ R}_{GS} = 50 \Omega; V_{GS} = 10 \text{ V}; \text{ T}_{j(init)} = 25 \text{ °C}; \text{ unclamped}; Fig. 3 $		-	-	372	mJ

[1] Continuous current is limited by package.

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5. Pinning information

Table 2.	Table 2. Pinning information								
Pin	Symbol	Description	Simplified outline	Graphic symbol					
1	G	gate	mb	D					
2	D	drain	$2 \circ 4$						
3	S	source	TO-220AB (SOT78)	G G M M M M M M M M M M M M M M M M M M					

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PSMN3R3-60PL	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78				

7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN3R3-60PL	PSMN3R3-60PL

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

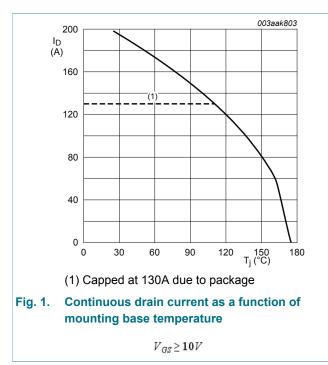
Symbol	Parameter	Conditions		Min	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	60	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	60	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	[1]	-	130	А
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>	[1]	-	130	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4		-	793	А

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Symbol	Parameter	Conditions		Min	Мах	Unit
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	293	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	diode		1			
I _S	source current	T _{mb} = 25 °C	[1]	-	130	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	793	А
Avalanche ru	ıggedness		1			
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} & {\sf I}_{\sf D} = 130 \; {\sf A}; {\sf V}_{sup} \le 60 \; {\sf V}; {\sf R}_{\sf GS} = 50 \; \Omega; \\ & {\sf V}_{\sf GS} = 10 \; {\sf V}; {\sf T}_{j({\sf init})} = 25 \; ^{\circ}{\sf C}; \; {\sf unclamped}; \\ & \underline{{\sf Fig. 3}} \end{split}$		-	372	mJ





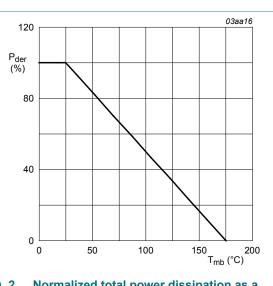
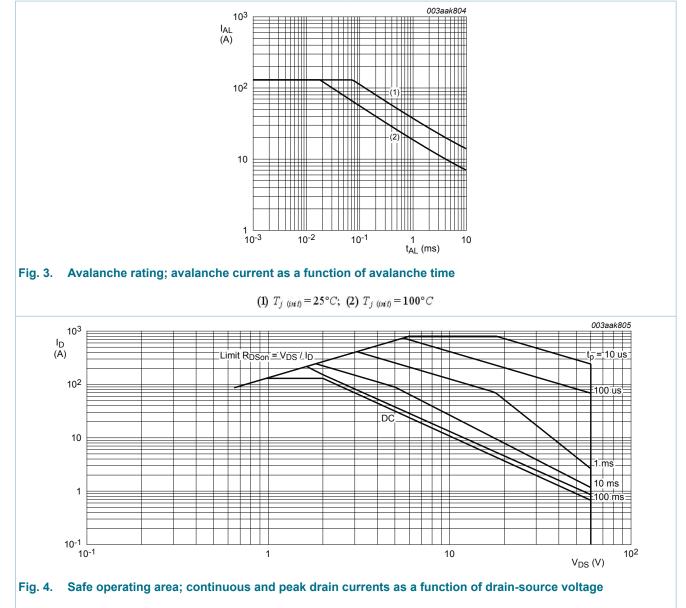


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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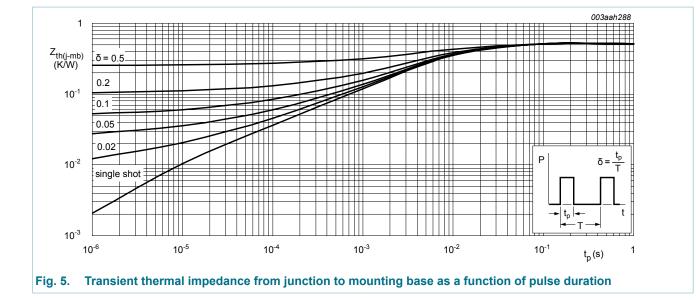
 $T_{mb} = 25^{\circ}C; I_{DM}$ is a single pulse

9. Thermal characteristics

Table 6. The	Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit	
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>		-	0.4	0.51	K/W	
R _{th(j-a)}	thermal resistance from junction to ambient	vertical in still air		-	60	-	K/W	

Table 6. Thermal characteristic

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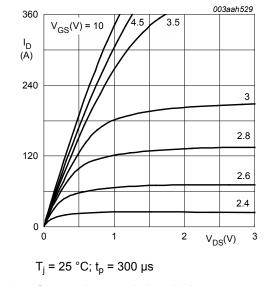


10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Static chara	acteristics	· · ·					
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	60	-	-	V	
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	54	-	-	V	
V _{GS(th)}	(th) gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	1.4	1.7	2.1	V	
			$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	2.45	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	0.5	-	-	V	
I _{DSS} drain leakage curre	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA	
		V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C	-	0.09	1	μA	
I _{GSS}	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA	
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA	
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	3	3.8	mΩ	
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	2.7	3.4	mΩ	
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 12; Fig. 11	-	-	7.5	mΩ	
R _G	gate resistance	f = 1 MHz	0.5	1	2	Ω	

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Dynamic cl	naracteristics	· · · · · ·				
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 48 V; V _{GS} = 5 V; <u>Fig. 13</u> ; Fig. 14	-	95	-	nC
		I_D = 25 A; V_{DS} = 48 V; V_{GS} = 10 V;	-	175	-	nC
Q _{GS}	gate-source charge	<u>Fig. 13; Fig. 14</u>	-	20	-	nC
Q _{GD}	gate-drain charge	-	-	31	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C; <u>Fig. 15</u>	-	10115	-	pF
C _{oss}	output capacitance		-	822	-	pF
C _{rss}	reverse transfer capacitance		-	427	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 45 V; R _L = 1.8 Ω; V _{GS} = 5 V; R _{G(ext)} = 5 Ω	-	54.2	-	ns
t _r	rise time		-	100	-	ns
t _{d(off)}	turn-off delay time		-	158	-	ns
t _f	fall time		-	109	-	ns
Source-dra	in diode		I			
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-	0.78	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 20 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;	-	43	-	ns
Q _r	recovered charge	V _{DS} = 25 V	-	67	-	nC





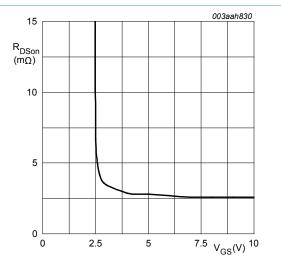


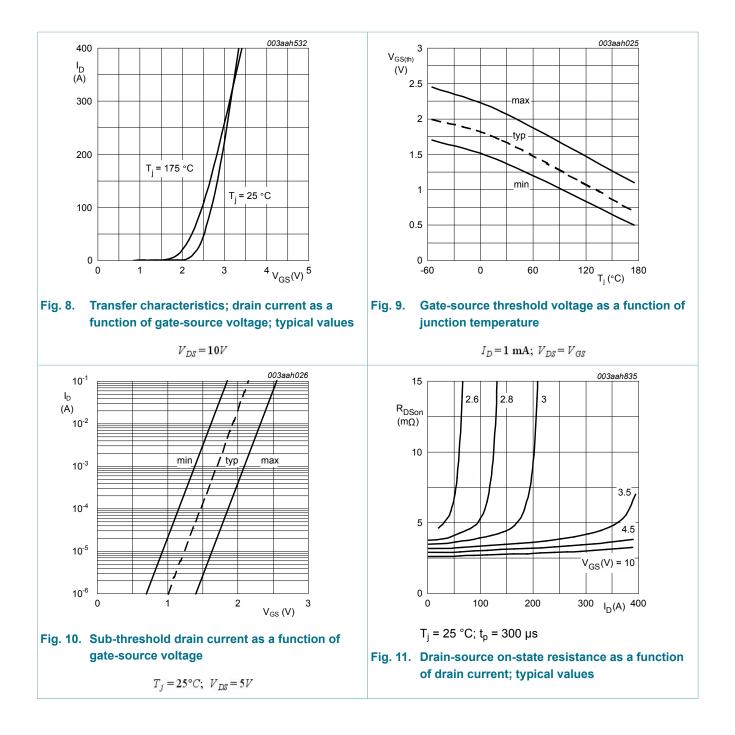
Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; \ I_D = 25A$

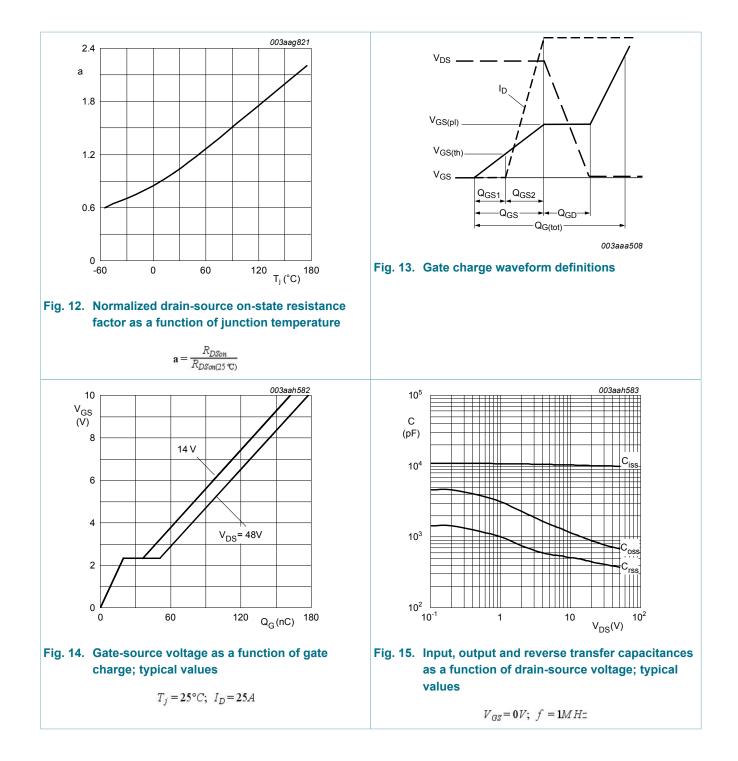
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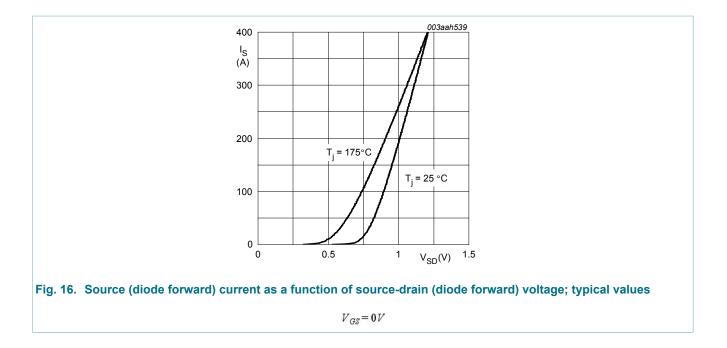


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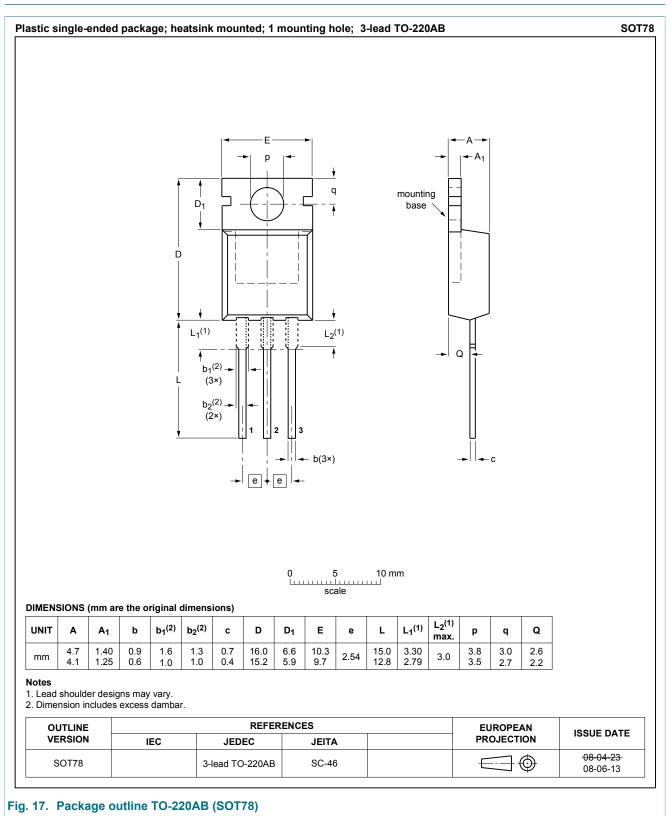
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11. Package outline



PSMN3R3-60PL

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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